



Solid State Devices, Inc.

14830 Valley View Blvd * La Mirada, Ca 90638

Phone: (562) 404-7855 * Fax: (562) 404-1773

ssdi@ssdi-power.com * www.ssdi-power.com

Designer's Data Sheet

FEATURES:

- High Surge Current
- High On State Current
- High Frequency up to 400 Hz operation
- Anode Common to Case
- Hermetically Sealed
- Replacement for part number 2N682 thru 2N692
- TX, TXV, S-Level Screening Available. Consult Factory

SFS682 thru SFS692

**25 AMPS
50 – 800 VOLTS
FAST SWITCHING
SILICON CONTROLLED
RECTIFIER**



TO-48

MAXIMUM RATINGS <small>(T_J = 25°C UNLESS OTHERWISE NOTED, R_{GK} = 1K Ω)</small>		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SFS682	V _{DRM}	50	Volts
	SFS683		100	
	SFS685	V _{RRM}	200	
	SFS688		400	
	SFS690		600	
	SFS692		800	
RMS On-State Current (180 ° Conduction Angle)	T _C = 80°C	I _{T (RMS)}	25	Amps
Average On-State Current	T _C = 80°C	I _{T (AV)}	16	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz, T _J initial = 25°C, t = 8.3 ms)	tp = 8.3 ms tp = 10 ms	I _{TSM}	210 200	Amps
Fusing Current	tp = 10 ms		I ² _T	200
Critical Rate of Rise of On-State Current Gate supply, I _g = 400 mA, dI _g /dt = 1A/μS		dI/dt	100	A / μs
Average Gate Power		P _{G (AV)}	1.0	Watts
Peak Gate Current	tp = 20 μs	I _{GM}	8	Amps
Peak Gate Voltage	tp = 20 μs	V _{GM}	15	Volts
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-49 to +150	°C
Thermal Resistance, Junction to Case		R _{θJC}	1.50	°C/W

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ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$ unless otherwise indicated)		Symbol	Min	Typical	Max	Unit
Peak Reverse Blocking Current (Rated V_{RRM})	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	I_{RRM}	—	—	20 3	μA mA
Peak Forward Blocking Current (Rated V_{DRM})	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	I_{DRM}	—	—	20 3	μA mA
Peak On-State Voltage ($I_F = 25\text{ A Peak}$, $t = 1\text{ ms}$, Duty Cycle $\leq 1\%$) ($I_F = 100\text{ A Peak}$, $t = 1\text{ ms}$, Duty Cycle $\leq 1\%$)		V_{TM}	—	—	2.05 2.25	Volts
Gate Trigger Current ($V_D = 12\text{ V}_{DC}$, $R_L = 33\ \Omega$)		I_{GT}	—	—	40	mA
Gate Trigger Voltage ($V_D = 12\text{ V}_{DC}$, $R_L = 33\ \Omega$)		V_{GT}	—	—	1.5	Volts
Gate off Voltage ($V_d = V_{drm}$, $I_g = 200\text{ mA}$, $dI_g/dt = 1.5\text{ A}/\mu\text{S}$, $T_j = 125^\circ\text{C}$)		V_{GD}	0.25	—	—	Volts
Latching Current ($I_g = 48\text{ mA}$)		I_L	—	50	—	mA
Holding Current ($I_T = 500\text{ mA}$, Gate Open)		I_H	—	30	70	mA
Critical Rate of Voltage Rise Linear slope up to $V_D = 67\%$ of V_{DRM})		dV/dt	200	—	—	V/μs
Commutated Turn-off Time ($I_g = 200\text{ mA}$, $dI_g/dt = 1.5\text{ A}/\mu\text{s}$)		t_{qt}	—	2	—	μs
Turn Off Time ($V_D = 67\%$ of V_{DRM} , $I_{TM} = 50\text{ A}$, $V_r = 50\text{ V}$, $dI_{TM}/dt = 30\text{ A}/\mu\text{s}$ $dV/dt = 20\text{ V}/\mu\text{S}$ $T_j = 125^\circ\text{C}$)		t_q	—	100	—	μs

NOTES:1/ Unless Otherwise Specified, All Electrical Characteristics @ $T_C = 25^\circ\text{C}$, $R_{GK} = 1\text{K}\ \Omega$.NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.**F3N0H****DATA SHEET #: SCR007A****DOC**



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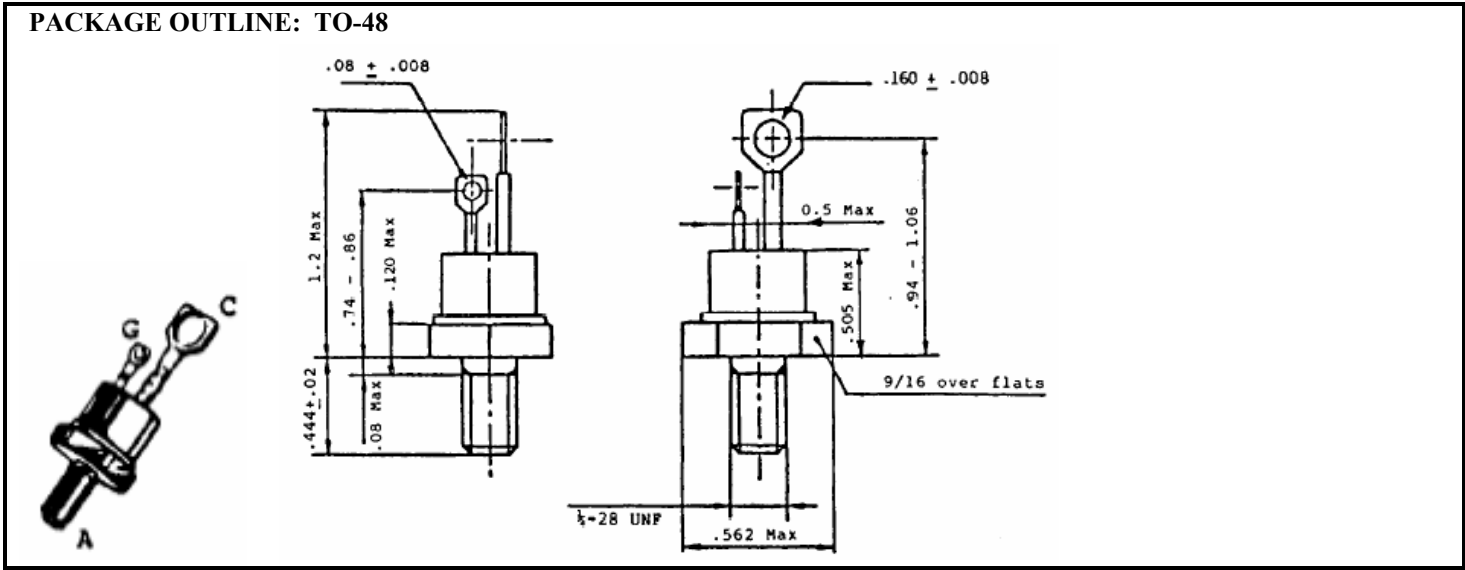
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SFS682 thru SFS692

PACKAGE OUTLINE: TO-48



Available Part Numbers:

SFS682; SFS683; SFS685; SFS688; SFS690; SFS692

SFS682/48; SFS683/48; SFS685/48; SFS688/48; SFS690/48; SFS692/48

PIN ASSIGNMENT (Standard)

Package	Cathode	Gate	Anode
TO-48 (/48)	Terminal 1	Terminal 2	Cathode